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Application Number	10/003,331
Filing Date	October 31, 2001
First Named Inventor	Slater
Group Art. Unit	
Examiner Name	
Attorney Docket Number	5000 113A

(use as many sheets as necessary)

Sheet	1	of	2
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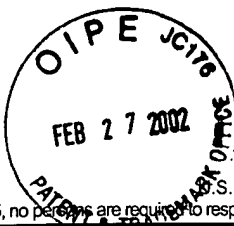
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 2 of 2

Complete if Known

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First Named Inventor	Slater
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Attorney Docket Number	5000.113A

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Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
dv	12	SPIEL (aka "Spiess"), Aluminum Implantation of p-SiC for ohmic contacts, First European Conference on Silicon Carbide and Related Materials (ECSCRM 96), Oct. 6-9, 1996, pp. 1414-1419, Vol. 6, no. 10, Elsevier, Switzerland	
	13	DEV ALOK ET AL, Low Contact Resistivity Ohmic Contacts to 6H-Silicon Carbide, Proceedings of the International Electron Devices Meeting, 1993, pp. 691-694, IEEE, New York	
	14	CHEN ET AL., Contact Resistivity of Re, Pt and Ta Films on n-Type Beta-SiC: Preliminary Results, Materials Science and Engineering, 01/01/1995, pp. 185-189, Vol. B29, no. 1/03, Elsevier Sequoia, Lausanne	
dv	15	PORTER ET AL, A critical review of ohmic and rectifying contacts for silicon carbide, Materials Science and Engineering, 11-01-1995, pp. 83-105, Vol. B34, no. 2/03, Elsevier Sequoia, Lausanne	

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